HIGH SPEED MULTIPORT MEMORY 82S12 (8x4 MULTIPORT RAM)

DIGITAL 8000 SERIES TTL/MEMORY

DESCRIPTION

The 82S12/112 is a Schottky TTL 32 bit multiport memory organized in 8 words of 4 bits each. The device is ideally suited for high speed accumulators and buffer memories.

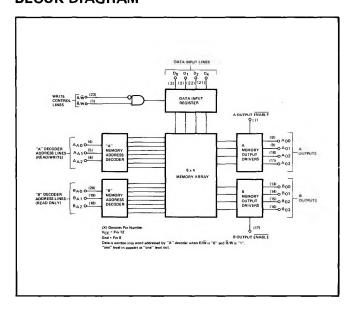
Stored data is addressed through 2 independent sets of 3-input decoders, and read out when the corresponding output enable line is low. Two separate word locations can, therefore, be read at the same time by enabling both the A and B output drivers. In addition, data can be read and written at the same time by utilizing the "A" address to specify the location of the word to be written, and the "B" address to specify the word to be read.

The 82S12/112 can be used in larger memory arrays since it includes all the control logic required to disable the chip and the outputs are open-collector devices suitable for "Wire-ORing."

FEATURES

- LOW CURRENT INPUT BUFFERS (-25µA TYPICAL)
- SEPARATE INPUT DECODERS FOR EACH WORD
- SEPARATE OUTPUT ENABLE LINES FOR EACH WORD
- OPEN COLLECTOR (82S12) OR TRI-STATE (82S112) **OUTPUTS**
- **2 WRITE ENABLE LINES**
- FAST ACCESS (20 ns TYPICAL)
- **USEFUL 8 × 4 ORGANIZATION**
- TTL COMPATIBLE
- NON INVERTING DATA LINES

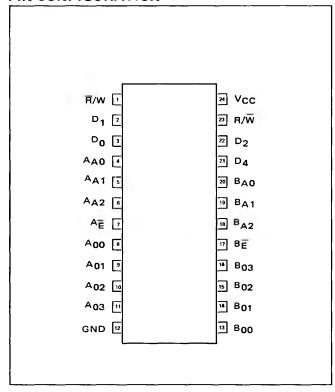
BLOCK DIAGRAM



APPLICATIONS

SCRATCH PAD MEMORY BUFFER MEMORY ACCUMULATOR REGISTER GENERAL REGISTER

PIN CONFIGURATION



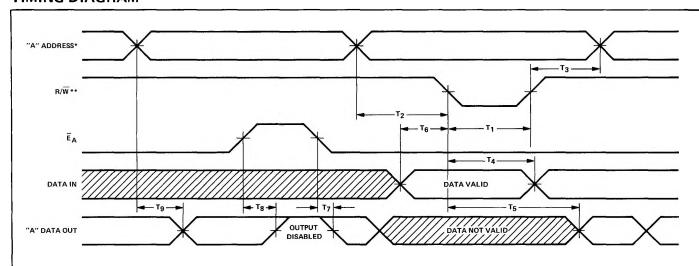
TRUTH TABLE

R/W	R/W	A OUTPUT ENABLE		MODE	OUTPUTS	
					A	В
0 0 0 0 1 1 1 1	X X X 1 1 1 0	1 1 0 0 1 1 0 0	1 0 1 0 1 0 1 0	Outputs Disabled Read Read Read Read Read Read Read Re	"1" Data Data "1" Data Data "1" The control of the	"1" Data "1" Data "1" Data "1" Data "1" Data "1" Data
1	0 0	0	1	Write Write	Data Being Written Data Being	"B" Address "1"

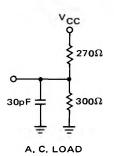
OBJECTIVE ELECTRICAL SPECIFICATIONS $0^{\circ}\text{C} \leqslant \text{T}_{A} \leqslant 75^{\circ}\text{C}$; -4.75 V \leqslant V_{CC} \leqslant 5.25 V.

CHARACTERISTICS	LIMITS			· ·	
CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Input "0" Current			-250	μА	V _{in} = 0.45 V
Input "1" Current			25	μА	V _{in} = 5.5 V
Input "0" Threshold Voltage		1	0.85	ľ	
Input "1" Threshold Voltage	2.0			l v	
Input Clamp Voltage	-1.2			l v	l _{in} = -18 mA
Output "0" Current	16	j		mA	V _{OU1} = 0.5 V
Output "0" Current	9.6				V _{out} = 0.45 V
Output "1" Voltage (825112)	2.6			Volts	l _{out} = -3.2 mA
Output Off Current (82\$12)			40	μΑ	V _{out} ≤ 5.5 V
Output Off Current (82S112)	-40		+40	μΑ	0.45 ≤ V _{out} ≤ 5.5 V
Power Consumption		110/550	160/840	mA/mW	Outputs Enabled
Write Pulse Width T ₁		15	30	ns	T _A = 25°C Only
Т1			45	ns	$0^{\circ}C \leq T_{\Delta} \leq 75^{\circ}C$
Address Set Up Time T ₂		10		ns	A .
Address Hold Time T ₃		0		ns	
Data Input Hold Time T ₄		15		ns	
Write Access Time T5		30		ns	
Data Input Set Up Time T6		5		ns	
Output Enable Time T ₇	1	10	20	ns	
Output Disable Time T8		10	20	ns	
Address Access Time Tg		20	30	ns	

TIMING DIAGRAM



- T₁ WRITE PULSE WIDTH Width of write pulse (when R/W="1" and R/W="0")
- T₂ ADDRESS SETUP TIME Required delay between beginning of valid Address and beginning of Write pulse.
- ${\rm T_3}$ $\,$ ADDRESS HOLD TIME Required delay between end of Write pulse and end of valid Address
- ${\rm T_4} = {\rm DATA\ INPUT\ HOLD\ TIME} {\rm Required\ delay\ between\ start\ of\ Write\ pulse\ and\ end\ of\ Valid\ Data\ input.}$
- T₅ WRITE ACCESS TIME Delay between beginning of Write pulse and Data Out at new value.
- T₆ DATA INPUT SET-UP TIME Required delay between beginning ov Valid Data Input and start of Write pulse.
- T₇ OUTPUT ENABLE TIME Dalay between beginning of Output Enable high and when Data Output becomes valid.
- T₈ OUTPUT DISABLE TIME Delay between when Output Enable becomes low and Data Output is in off state
- Tg ADDRESS ACCESS TIME Delay between beginning of Valid Address (with Output Enable high, R/W high and R/W low) and when Data Output becomes valid.



NOTES

[&]quot;B" Address functions identically in read mode. No write mode through B address decoder.

^{**}R/W input is either the reverse of R/W or held high.

Outputs can be disabled during write cycle to penetrate a known output state during write.